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# Nb<sub>3</sub>Sn FOR RADIO FREQUENCY CAVITIES\*

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## Abstract

In this article, the suitability of Nb<sub>3</sub>Sn to improve the performance of superconducting Radio-Frequency (RF) cavities is discussed. The use of Nb<sub>3</sub>Sn in RF cavities is recognized as an enabling technology to retain a very high cavity quality factor ( $Q_0$ ) at 4.2 K and to significantly improve the cavity accelerating efficiency per unit length ( $E_{acc}$ ). This potential arises through the fundamental properties of Nb<sub>3</sub>Sn. The properties that are extensively characterized in the literature are, however, mainly related to improvements in current carrying capacity ( $J_c$ ) in the vortex state. Much less is available for the Meissner state, which is of key importance to cavities. Relevant data, available for the Meissner state is summarized, and it is shown how this already validates the use of Nb<sub>3</sub>Sn. In addition, missing knowledge is highlighted and suggestions are given for further Meissner state specific research.

## INTRODUCTION

Linear accelerators utilize a linear array of RF cavities and become increasingly long, with lengths up to the tens of kilometer range, to achieve particle energies in the GeV to TeV energy range that is of present High Energy Physics (HEP) interest. Such systems will require on the order of 20,000 RF cavities. Improving the accelerating voltage per unit length will result in tremendous cost savings, since the required length to achieve a given beam energy in a linear accelerator is inversely proportional to the electric field that can be generated per unit length. In addition, power requirements are significant, ranging from 100 to 250 MW for a 500 GeV linear accelerator.

The main figures of merit for RF cavities are the quality factor  $Q_0$  (defined by the ratio between the energy stored in the cavity and the energy loss in one RF period) and its average accelerating field  $E_{acc}$ .  $Q_0$  values as high as  $10^{11}$  have been achieved in superconducting cavities. Superconducting cavities exhibit approximately a factor  $10^6$  higher  $Q_0$  than normal conducting cavities due to the reduced microwave surface resistance. Even when accounting for cooling penalties the required input power is still about a factor  $10^3$  lower when using superconducting cavities instead of normal conducting cavities, saving drastically in operating costs. The International Technology Recommendation Panel of the International Committee for Future Accelerators therefore, amongst other considerations, selected superconducting RF cavities above normal conducting cav-

ities as the preferred technology for future linear accelerators [1].

The efficiency of a RF cavity is usually depicted by plotting  $Q_0$  as function of  $E_{acc}$ . For an ideal superconducting cavity,  $Q_0$  remains constant with increasing  $E_{acc}$  and collapses when a maximum  $E_{acc}$  is reached. This point is determined by the magnetic components of the RF standing wave. Once the magnetic component reaches a certain threshold value, vortices penetrate the superconductor and the Meissner state is lost. Vortices that move inside the superconductor dissipate energy and cause the cavity to ‘quench’. Even though vortices can be – elastically – ‘pinned’ by material imperfections, their oscillations in an RF field will still cause dissipations [2]. Hence, vortex penetration has to be prevented to retain a high  $Q_0$  and a cavity has to operate in the Meissner state.

In Type-II superconductors, vortex penetration becomes energetically favorable at the bulk lower critical magnetic field  $H_{c1}$ . However, in magnetic fields which are parallel to the surface, vortices have to overcome the Bean-Livingston positive surface energy barrier to enter the superconductor [3]. The Meissner state can therefore persist metastably beyond  $H_{c1}$ , up to the so-called superheating field  $H_{sh}$ , at which the surface barrier disappears. For Type-II superconductors with a Ginzburg-Landau (GL) parameter  $\kappa \gg 1$ ,  $H_{sh} \cong 0.75H_c$ , i.e. 75% of the thermodynamic critical field  $H_c$  [4], and its magnitude is thus the main determinant for  $E_{acc}$ . Note that in practice  $H_{sh}$  is not necessarily reached, due to earlier vortex penetration at surface irregularities [5] and demagnetization effects of transverse magnetic field components [6].

Cavity RF losses, in the absence of vortices, are mainly determined by the RF surface resistance ( $R_s$ ), which is usually represented as a summation of the Bardeen-Cooper-Schrieffer (BCS) surface resistance  $R_{BCS}$  and a residual resistance term ( $R_{res}$ ).  $R_{res}$  is usually on the order of a few n $\Omega$ . Provided that the surface is clean and properly manufactured,  $R_s$  is usually dominated by  $R_{BCS}$ , which can be written as [7]:

$$R_{BCS} \propto \lambda_{eff}^3 \omega^2 \ell \exp(-\Delta/k_B T), \quad (1)$$

where, at  $T = 0$  [8]:

$$\lambda_{eff} = \lambda_L \sqrt{1 + \xi_0/\ell}. \quad (2)$$

$\lambda_L$  and  $\lambda_{eff}$  are the London and effective penetration depths respectively,  $\omega$  is the frequency,  $\ell$  is the mean free path,  $\xi_0$  is the BCS coherence length (far below the critical temperature ( $T_c$ ),  $\xi_0 \cong \xi_{GL}$ , the GL coherence length [8]),  $\Delta$  is the superconducting energy gap,  $k_B$  is the Boltzmann constant, and  $T$  is the temperature.  $R_{BCS}$  reduces exponentially with  $T_c$  since  $\Delta = Ck_B T_c$ , where  $C = 1.76$

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in the weak coupling limit and increasing towards stronger interaction. In the clean limit ( $\ell \gg \xi_0$ ),  $\lambda_L \sqrt{1 + \xi_0/\ell}$  reduces to  $\lambda_L$ . In the dirty limit ( $\ell \ll \xi_0$ ) it can be shown that low  $R_{BCS}$  values can be obtained for low values of the normal state resistivity  $\rho_n$  [9]. In general, however,  $R_{BCS}$  is minimal for  $\xi_0 \cong \ell$  [7]. Also, since the Ginzburg-Landau parameter  $\kappa = \lambda_{eff}/\xi_{GL}$ ,  $R_{BCS}$  will be significantly reduced in low- $\kappa$  superconductors. This requirement is contrary to  $J_c$  optimizations for which a high upper critical field  $H_{c2}$  is desired, since  $H_{c2} = \kappa\sqrt{2}H_c$ .

A high  $E_{acc}$ , high  $Q_0$  superconducting RF cavity thus requires a superconductor with a high  $H_c$  (i.e. a high  $H_{sh}$ ) and large  $\Delta$  (i.e. high  $T_c$ ), a low  $\lambda_{eff}$  and  $\rho_n$  (or more exact  $\xi_0 \cong \ell$ ), and a perfect smooth surface to retain a high  $H_{sh}$ .

## NIOBIUM

Of the known practically usable superconductors, Nb has the highest bulk  $\mu_0 H_{c1} = 170$  mT and, hence, is used for RF cavity applications. An overview of relevant material properties for Nb is presented in Table 1. The parameters are given at  $T = 0$  K. Since Nb cavities will be mainly operated at about 2 K and derivatives for  $T \rightarrow 0$  are zero, the zero temperature values can be expected to be sufficiently accurate. Nb cavities can exhibit a drop in  $Q_0$  towards higher  $E_{acc}$ . This so-called  $Q$ -drop is not fully understood, but appears to be related to Nb-oxides at the cavity surface [10]. For bulk cavities, the  $Q$ -drop can be significantly reduced by baking the cavity at about 500 °C, which presumably redistributes the oxygen. For thin Nb film on Cu cavities the  $Q$ -drop cannot, for now, be prevented. The present state-of-the-art bulk Nb cavities exhibit, at  $T = 2$  K, a  $Q_0$  above  $10^{10}$  until an  $E_{acc}$  of about 50 MV/m, at which point the cavities quench. Note that Nb cavities have to be operated in superfluid Helium (i.e. below 2.2 K) at frequencies above about 1 GHz, since at higher temperatures the BCS losses become too excessive [11], Eq. (1). An  $E_{acc} \cong 50$  MV/m corresponds closely to the magnetic field limit for Nb. Note that differences between achieving  $H_{c1}$ ,  $H_{sh}$  or  $H_c$  are virtually indistinguishable for Nb. Nevertheless, achieving the magnetic field limitation for Nb cavities means that Nb is exhausted for a further increase in the accelerating voltage.

## NIOBIUM-TIN

### *Off-stoichiometry, morphology and strain*

The characteristic parameters for close to stoichiometric  $Nb_3Sn$  are presented in Table 1. As for Nb, the values are given at  $T = 0$  to provide a direct comparison. For 2 K operation these can be expected to be sufficiently accurate. For higher temperatures (e.g. 4.2 K), their values can be calculated since for  $Nb_3Sn$  all temperature dependence is accurately known [13]. A review of the available literature for composition, morphology and strain dependence of the

Table 1: Characteristic parameters of Nb and  $Nb_3Sn$

Property	Nb	$Nb_3Sn$ <sup>a</sup>
$T_c$ [K]	9.2	18
$\mu_0 H_{c1}(0)$ [T]	0.17	0.038
$\mu_0 H_c(0)$ [T]	0.2	0.52
$\mu_0 H_{c2}(0)$ [T]	0.4	30
$\xi_{GL}(0)$ [nm] <sup>b</sup>	29	3.3
$\lambda_{eff}(0)$ [nm] <sup>c</sup>	41	135
$\kappa(0)$ <sup>d</sup>	1.4	41
$\Delta(0)$ [meV] <sup>e</sup>	1.4	3.4
$\rho_n$ [ $\mu\Omega\text{cm}$ ]	< 100(VERIFY!)	< 20

<sup>a</sup> Approaching stoichiometry.

<sup>b</sup> From  $\sqrt{\phi_0 / (2\pi\mu_0 H_{c2}(0))}$  [8].

<sup>c</sup> From  $\sqrt{\phi_0\mu_0 H_{c2}(0) / (4\pi H_c^2)}$  [8].

<sup>d</sup> From  $\kappa(0) = \lambda_{eff}(0) / \xi_{GL}(0)$ .

<sup>e</sup> From  $\Delta(0) = Ck_B T_c$ , assuming a weak coupling limit for pure Nb and using  $C = 2.2$  for  $Nb_3Sn$  [12].

critical parameters is presented in [12]. Relevant results will here be summarized.

The Nb-Sn intermetallic has a range of stable compositions from about 18 to 25 at.% Sn, generally referred to as the A15 phase. The A15 phase can be formed from the melt above 930 °C, or at lower temperatures through a solid-state reaction between Nb and the Sn-rich line compounds  $Nb_6Sn_5$  and  $NbSn_2$ . Most available literature describing optimization of  $Nb_3Sn$  technology focuses on DC applications that utilize large transport currents. Requirements for DC applications are, however, significantly different (fine grains and slightly off-stoichiometric, dirty  $Nb_3Sn$  for increased pinning efficiency and high  $H_{c2}$ ) than for RF superconductivity (large grains, approaching stoichiometry and clean for high  $T_c$ ,  $H_{c1}$  and low  $\rho_n$ ).

For transport current applications the A15 phase is usually formed in the presence of a few percent Cu which catalyzes the formation reaction by destabilizing the Sn-rich line compounds combined with a – suggested – lowering of the melt temperature. This allows for a lower temperature formation reaction, typically between 650 and 700 °C, which is in transport applications required to prevent grain growth, since the grain size increases exponentially with reaction temperature [14].

The critical parameters depend strongly on the Sn content in the A15 phase. From measurements, it is known that from 18 to 25 at.% Sn,  $T_c$  changes from about 6 K to 18.3 K,  $\Delta(0)$  from about 1 to 3.4 meV, and  $\mu_0 H_{c2}$  ranges from about 6 to 30 T. Fortunately, there are strong indications that the stoichiometric composition is preferred towards lower temperatures (< 1000 °C), i.e. the perfect ordered state apparently represents the lowest total energy. Above about 24.5 at.% Sn, however, the cubic A15 phase becomes unstable below  $T_m \cong 43$  K and the lat-

tice undergoes a spontaneous cubic to tetragonal distortion ( $c/a \cong 1.0035$ ). This tetragonal distortion causes a reduction in  $T_c$  of about 0.2 K and reduces  $\mu_0 H_{c2}$  from 30 T at 24.5 at.% Sn to 20 T at stoichiometry. The normal state resistivity ranges from about 90  $\mu\Omega\text{cm}$  at 18 at.% Sn to below 5  $\mu\Omega\text{cm}$  for a stoichiometric single crystal.

Influences of grain size are mainly reported in relation to the maximum pinning force in the vortex state. Intuitively, the critical fields and temperature are not expected to be significantly influenced by grain size (though boundary effects could influence the overall  $\Delta$ , as is known from tunneling experiments) but, to the author's knowledge, no specific results are available on the dependence of  $T_c$  and critical fields on grain size. Grain size most probably influences  $\rho_n$  but again, to the author's knowledge, no specific results which relate the resistivity to grain size are available.

Strain, or lattice distortions in general, strongly influence the critical parameters of the A15 phase and indications are that the effects of strain are increased towards higher ordered (i.e. Sn-rich) A15 compositions. In general, optimal properties are obtained in the strain free state and the presence of strain will cause a reduction of the critical parameters. Strain, whether originating from neighboring materials with a different thermal contraction and/or lattice mismatch or originating from lattice imperfections, has therefore to be prevented. In [12] a correlation is suggested between off-stoichiometry, strain, thermal disorder, irradiation, tetragonal distortions, etc. All affect the long range order and thus Nb-chain continuity. In general, the superconducting properties of relevance for RF applications appear optimal when perfect ordering is achieved. In this sense, a slight off-stoichiometry at 24.5 at.% Sn could be preferable above a tetragonal distortion at stoichiometry. For transport current applications this is specifically true due to the large reduction of  $H_{c2}$  that results from only a slight tetragonal distortion of the lattice.

The above summary points out the importance to manufacture A15 in (close to) stoichiometric compositions and to prevent any strain. Of the parameters of relevance to RF superconductivity, only compositional influences on  $T_c$ ,  $\Delta$  and  $\rho_n$  are available. Unfortunately, to the author's knowledge, no investigations on the dependence of  $H_c$  and  $H_{c1}$  on composition are available. In addition, it will be desirable to determine the relation of grain size to  $\rho_n$ . Since a lower temperature A15 formation reaction is preferable for large scale cavity manufacture, it will also be desirable to investigate the effect of the presence of a few percent Cu on  $\rho_n$ . Intuitively, one might expect Cu to increase scattering and, hence, increase  $\rho_n$ . Nevertheless, since Cu is insoluble in A15, it is present only at the grain boundaries rendering prediction of its effect on  $\rho_n$  less straightforward. Even though limited information is available for off-stoichiometric compositions, the benefits of Nb<sub>3</sub>Sn compared to Nb can be demonstrated for compositions approaching stoichiometry and it will be discussed below how Nb<sub>3</sub>Sn can be beneficial for application in RF

cavities in bulk form and specifically as thin film.

### Potential of Nb<sub>3</sub>Sn for bulk cavities

The prime parameter for RF losses in bulk cavities is  $R_{BCS}$ . From (1), due to an exponential dependence on  $T_c$ , the two times higher  $T_c$  with respect to Nb will result in a smaller  $R_{BCS}$  and therefore higher  $Q_0$ , despite the larger penetration depth. Demonstrated specifically at  $T = 4.2$  K (and 500 MHz): For close to stoichiometric Nb<sub>3</sub>Sn (i.e. 24.5 at.% Sn),  $\rho_n$  drops to below 20  $\mu\Omega\text{cm}$  as a result of perfect ordering of the stoichiometric phase, providing the potential for  $R_{BCS} < 2$  n $\Omega$  (from the nomogram in [9]), which is significantly lower than around 55 n $\Omega$ , as provided by Nb cavities.  $Q_0$  for bulk Nb<sub>3</sub>Sn cavities thus has the potential to be significantly higher than found in Nb cavities. Nb<sub>3</sub>Sn cavities, manufactured through a Sn vapor technique, indeed exhibit a  $Q_0$  that is a factor two larger than for Nb at  $T = 2$  K [15]. More importantly, however, at  $T = 4.2$  K,  $Q_0$  is nearly two orders of magnitude larger for Nb<sub>3</sub>Sn than for Nb and comparable to Nb at  $T = 2$  K, due to the ratio  $T_c/T$  in (1). This demonstrates the ability for Nb<sub>3</sub>Sn cavities to operate at  $T = 4.2$  K, i.e. much more cost effective than Nb at superfluid Helium at  $T = 2$  K. It should be noted, that Nb<sub>3</sub>Sn layers which are grown through such a diffusion process, exhibit composition gradients [16] that are very comparable to gradients found in wires [17] and similar property distributions can therefore be expected.

The thermodynamic critical field of Nb<sub>3</sub>Sn is much higher than for Nb (Table 1), yielding the potential to more than double  $E_{acc}$ . Unfortunately, high  $Q_0$  values in Nb<sub>3</sub>Sn cavities are only retained up to about 15 MV/m, after which a linear  $Q$ -drop is observed [15] and the highest  $E_{acc}$  achieved is limited to below 30 MV/m. This means that, for now, bulk Nb<sub>3</sub>Sn cavities do not reach their theoretical limit ( $> 100$  MV/m). This might be attributable to inhomogeneity effects, surface impurities, or simply a shape effect causing a lowered vortex penetration field (i.e. surface irregularities and/or perpendicular field components), causing the penetration field to be closer to the bulk  $H_{c1}$  than to  $H_{sh}$ . It should be noted that, even though the presence of a superheating field can be demonstrated theoretically, it is not possible to verify whether  $H_{sh}$  has indeed been achieved in a practical Nb cavity, as a result of the closeness of  $H_{c1}$ ,  $H_{sh}$  and  $H_c$ .

### Potential of Nb<sub>3</sub>Sn thin films

If a superconducting film is deposited with a thickness  $d$  that is smaller than the penetration depth, the Meissner state can retain at magnetic fields that are much higher than the bulk  $H_{c1}$ , resulting from an increased parallel  $H_{c1}$  in a thin film with  $d < \lambda_{eff}$ , given by [18]:

$$\mu_0 H_{c1} = \frac{2\phi_0}{\pi d^2} \ln \frac{d}{\xi} \quad (3)$$

where  $\tilde{\xi} = 1.07\xi_{GL}$ . For example, a thin  $\text{Nb}_3\text{Sn}$  film with  $d = 20$  nm increases  $H_{c1}$  of  $\text{Nb}_3\text{Sn}$  to 5.7 T. In a  $\text{Nb}_3\text{Sn}$  thin film deposited on a normal conductor, however, small perpendicular magnetic field components will destroy the Meissner state since  $H_{c1}$  will be reduced by a demagnetization factor  $d/w$ , where  $w$  represents the width of the  $\text{Nb}_3\text{Sn}$  thin film [6]. Nevertheless, the increased  $H_{c1}$  of a thin  $\text{Nb}_3\text{Sn}$  film can be applied to shield bulk Nb from magnetic fields. For example, following [6], if a Nb cavity that can withstand an internal magnetic field of 150 mT is coated with an insulating film and a 50 nm  $\text{Nb}_3\text{Sn}$  layer, the external magnetic field can be as high as about 320 mT. Hence, a  $\text{Nb}_3\text{Sn}$  film coating more than doubles the vortex penetration field of a Nb cavity, potentially enabling an  $E_{acc}$  of order 100 MV/m. Obviously, these ideas are very promising for a reduction of the required length of a linear accelerator, but involve significant technological challenges and their practical validity remains to be demonstrated.

## SUGGESTIONS FOR FUTURE RESEARCH

The potential of  $\text{Nb}_3\text{Sn}$  to enhance the prime parameters for superconducting cavities, i.e.  $Q_0$  and  $E_{acc}$  with respect to Nb is evident. Nevertheless, further research is required to determine the practical validity. Since most available literature on  $\text{Nb}_3\text{Sn}$  focusses on transport current capacity optimizations, specific research that is specifically targeted at RF superconductivity is desired.

**Composition dependence of  $H_{c1}$  and  $H_c$**  Compositional inhomogeneities are inevitable in diffusion based A15 formation processes and, even though it might be possible to create – quasi – homogeneous thin films, stoichiometry is not necessarily the optimal composition (minimum  $R_{BCS}$  for  $\xi \cong \ell$ , tetragonal distortions). It is therefore required to know how the key critical magnetic fields,  $H_{c1}$  and  $H_c$  vary with composition.

**Presence of Cu** The fact that a few percent Cu can significantly reduce the A15 formation temperature can be very desirable for large scale cavity manufacture. It is evident that Cu is insoluble in the A15 phase and most literature suggests that Cu therefore is present only at the grain boundaries. It is unclear, however, how a – limited – presence of Cu influences  $\rho_n$ . This should be investigated to find out whether a lower temperature formation reaction is a realistic option for cavity manufacture.

**Effects of grain size** Granularity will negatively affect  $\rho_n$ . It is not known for  $\text{Nb}_3\text{Sn}$ , however, how severe this effect is and therefore how much care should be taken to manufacture large grains. This is related to the presumed presence of Cu at the grain boundaries or, more general, what exactly is present at the grain boundaries. From transport current optimizations it is clear

that the grain boundaries act as the main pinning centers, but it is unknown what causes minima in the superconducting wave function at grain boundaries. Investigating specifically the morphology and composition of grain boundaries is a subject that only recently emerged in the transport current community, but is also of major importance to the RF community. Investigating how  $\rho_n$  varies with grain size and which physics at grain boundaries presumably increases  $\rho_n$  is therefore important to both communities.

**Manufacturing issues** Experiments need to be performed to investigate to what extent  $\text{Nb}_3\text{Sn}$  can be formed in bulk and thin films, with properties that are optimized for RF superconductivity applications. Bulk materials can be manufactured from powder or through diffusion based processes. The Wuppertal  $\text{Nb}_3\text{Sn}$  cavities [15] demonstrate the possibility to manufacture large scale bulk systems. Nevertheless, small-scale bulk samples are useful for basic property characterizations ( $H_{c1}$ ,  $H_c$ ,  $\rho_n$ , etc.), provided they are sufficiently homogeneous and dense.

Thin films with well-defined properties have been successfully manufactured already in the late 1970's (see e.g. the work of Beasley and co-authors referenced in [12]) and proved very useful in investigating property dependencies on composition. Using more modern and promising techniques such as vacuum arc deposition [19] could be a route to single- and multi-layer thin films that incorporate  $\text{Nb}_3\text{Sn}$ . Specifically vacuum arc deposition is highlighted since this technique results in very dense films with a nano-meter scale surface roughness on Nb films [20] and appears scalable to cavity-size manufacture. However, its applicability for  $\text{Nb}_3\text{Sn}$  has not yet been investigated.

## SUMMARY

It is clear that  $\text{Nb}_3\text{Sn}$  has significant potential for RF cavity applications, due to the materials' superior intrinsic properties compared to Nb. Specifically for bulk cavities, it has the potential to increase the cavity quality factor at 4.2 K about two orders of magnitude above Nb values and to more than double the accelerating efficiency per unit length. In multi-layer coated bulk Nb cavities, it has the potential to shield the bulk from vortex penetration, rendering even higher gains in accelerator efficiency per unit length possible. Further research is required, however, to investigate to what extent these promises can be fulfilled.

Much literature is available on the fundamental properties of  $\text{Nb}_3\text{Sn}$ , but most is specifically focussed on transport current improvements. Important data on fundamental properties for RF superconductivity are missing, specifically in relation to  $\text{Nb}_3\text{Sn}$ 's composition dependence. Further research is therefore suggested to expand the available results towards fundamental properties that are of key importance to RF superconductivity.

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